



# TIP41A/41B/41C TIP42A/42C

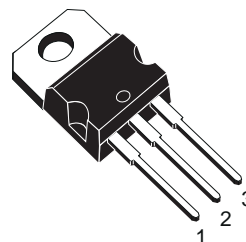
## COMPLEMENTARY SILICON POWER TRANSISTORS

### ■ COMPLEMENTARY PNP - NPN DEVICES

#### DESCRIPTION

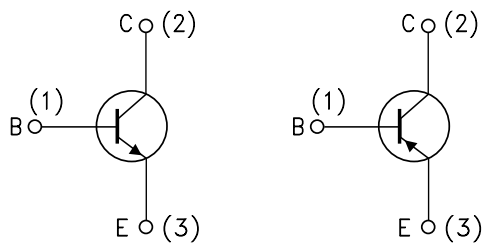
The TIP41A, TIP41B and TIP41C are silicon Epitaxial-Base NPN power transistors mounted in Jedec TO-220 plastic package. They are intended for use in medium power linear and switching applications.

The TIP41A and TIP41C complementary PNP types are TIP42A and TIP42C respectively.



TO-220

#### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		NPN PNP	TIP41A TIP42A	TIP41B TIP42B	TIP41C TIP42C	
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )		60	80	100	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )		60	80	100	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )		5			V
$I_C$	Collector Current		6			A
$I_{CM}$	Collector Peak Current		10			A
$I_B$	Base Current		3			A
$P_{tot}$	Total Dissipation at $T_{case} \leq 25^\circ C$ $T_{amb} \leq 25^\circ C$		65			W
			2			W
$T_{stg}$	Storage Temperature		-65 to 150			$^\circ C$
$T_j$	Max. Operating Junction Temperature		150			$^\circ C$

For PNP types voltage and current values are negative.

## TIP41A/TIP41B/TIP41C/TIP42A/TIP42C

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.92	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5	°C/W

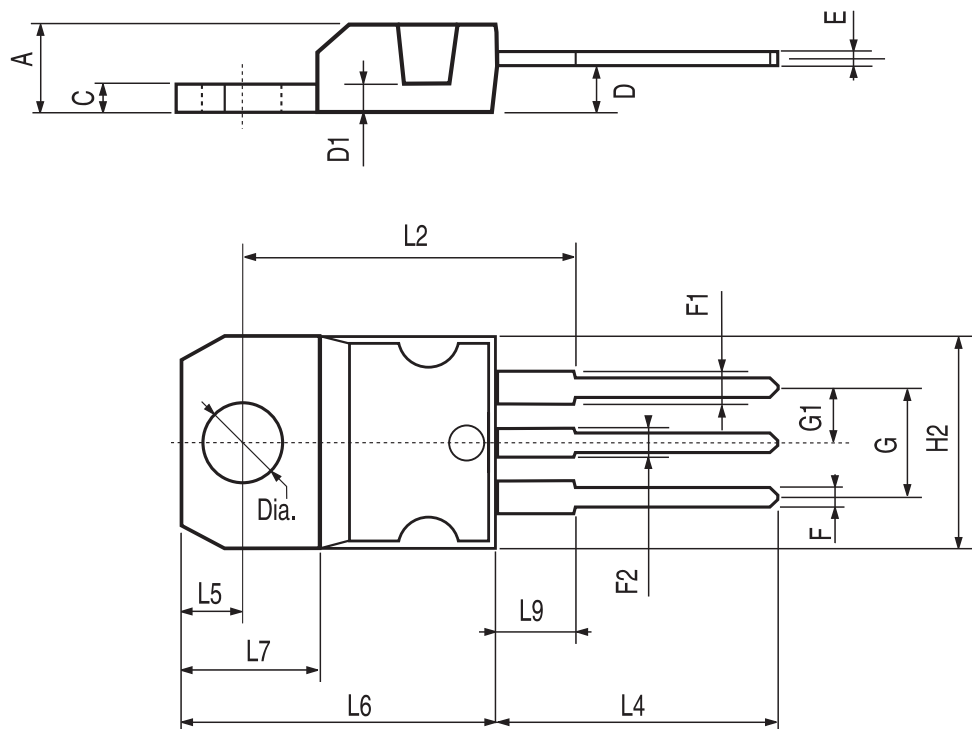
### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	for <b>TIP41A/42A</b> V <sub>CE</sub> = 30 V for <b>TIP41B/41C/42C</b> V <sub>CE</sub> = 60 V			0.7 0.7	mA mA
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	for <b>TIP41A/42A</b> V <sub>CE</sub> = 60 V for <b>TIP41B</b> V <sub>CE</sub> = 80 V for <b>TIP41C/42C</b> V <sub>CE</sub> = 100 V			0.4 0.4 0.4	mA mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			1	mA
V <sub>CEO(sus)</sub> *	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 30 mA for <b>TIP41A/42A</b> for <b>TIP41B</b> for <b>TIP41C/42C</b>	60 80 100			V V V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6 A I <sub>B</sub> = 0.6 A			1.5	V
V <sub>BE(on)</sub> *	Base-Emitter Voltage	I <sub>C</sub> = 6 A V <sub>CE</sub> = 4 V			2	V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 0.3 A V <sub>CE</sub> = 4 V I <sub>C</sub> = 3 A V <sub>CE</sub> = 4 V	30 15		75	
h <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 0.5 A V <sub>CE</sub> = 10 V f = 1 KHz I <sub>C</sub> = 0.5 A V <sub>CE</sub> = 10 V f = 1 MHz	20 3			

\* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %  
For PNP types voltage and current values are negative.

## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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